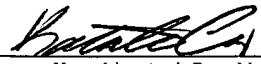


IFW

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hyodo, et al.
Appl. No. : 10/644,195
Filed : August 20, 2003
For : METHOD OF FORMING SILICON-CONTAINING INSULATION FILM HAVING LOW DIELECTRIC CONSTANT AND LOW FILM STRESS
Examiner : Yennhu B Huynh
Group Art Unit : 2813

CERTIFICATE OF MAILING
I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on
February 3, 2005
(Date)

Katsuhiro Arai, Reg. No. 43,315

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

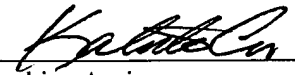
Dear Sir:

This is in response to the communication from the Examiner mailed January 11, 2005. In response to the species election requirement set forth in the communication, Applicant elects to Species I, drawn to a method for forming a silicon containing insulation film, to which the claims shall be restricted if no generic claim is finally held to be allowable. Claims 1-17 are readable on the elected species. This election is made without traverse.

No fees are believed due for the present Amendment, however, should any fees be due, please charge them to our deposit account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: February 3, 2005 By: 
Katsuhiro Arai
Registration No. 43,315
Attorney of Record
Customer No. 20,995
(949) 760-0404